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1	contact hole;
2	a counter electrode formed on said second substrate; and
3	a liquid crystal layer between said first and second substrate being driven by an
4	electric field between said pixel electrode and said counter electrode to thereby make a
5	display,
6	wherein said color filter is formed directly on said first substrate in most of a light
7	transmission region within a pixel area surrounded by said scanning lines and said signal
8	lines, and a stack of layers comps
9	a stacking layer of said passivation-film-and-said color filter is formed near said
10	contact hole, and
11	said overcoat layer is formed on said filter, and
12	said pixel electrode is formed on said color filter.
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1	2. (Twice Amended) An active matrix liquid crystal display device comprising:
/ 2	a first substrate and a second substrate, at least one of said first and second substrate
3	being transparent;
	a plurality, of scanning lines formed on said first substrate;
5	a plurality of signal lines formed on said first substrate crossing said plurality of
6	scanning lines in a matrix manner;
7	a plurality of thin film transistors formed at each of intersections of said scanning
8	lines and said signal lines;
9	a passivation film formed on said thin film transistors;
10	at least one color filter formed on said first substrate;
11	an overcoat layer formed on said color filter;
12	a plurality of pixel electrodes connected to each of said thin film transistors through a
13	contact hole;
14	a counter electrode formed on said second substrate; and
15	a liquid crystal layer between said first and second substrate being driven by an
16	electric field between said pixel electrode and said counter electrode to thereby make a
17	display,

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said thin film transistors; and

film electrically connected through said contact hole.

wherein said color filter is formed directly on said first substrate in most of a light transmission region within a pixel area surrounded by said scanning lines and said signal lines, and a stacking layer of said passivation film, said color filter and said overcoat layer is formed near said contact hole, and said pixel electrode is formed on said overcoat layer. 6. (Twice Amended) A method of manufacturing an active matrix liquid crystal display 2 device, the method comprising: forming a plurality of scanning lines on a first substrate; 3 forming a plurality of signal lines crossing the plurality of scanning lines in a matrix manner; forming a plurality of thin film transistors at intersections of the plurality of scanning lines and the plurality of signal lines, respectively; forming a pixel electrode connected to said thin film transistors; 9 forming a counter electrode on a second substrate; 10 injecting a liquid crystal between said first substrate and said second substrate and 11 sealing the liquid crystals, 12 wherein said method further comprises: forming a passivation film to protect each of said thin film transistors; 13 14 removing part of a gate insulating layer and said passivation film of each of 15 said thin film transistors in a region surrounded by said signal lines and said scanning 16 lines; 17 forming a color filter comprising a photosensitive color resist; forming a contact hole in said color filter and said passivation film on each of 18

7. (Twice Amended) A method of manufacturing an active matrix liquid crystal display

forming a plurality of pixel electrodes comprising a transparent conductive

2	device, the method comprising:
3	forming a plurality of scanning lines on a first substrate;
4	forming a plurality of signal lines crossing the plurality of scanning lines in a matrix
5	manner;
6	forming a plurality of thin film transistors at intersections of the plurality of scanning
7	lines and the plurality of signal lines, respectively;
8	forming a pixel electrode connected to said thin film transistors;
9	forming a counter electrode on a second substrate;
10	injecting liquid crystal between said first substrate and said second substrate and
11	sealing the liquid crystals,
12	wherein said method further comprises:
13	forming a passivation film to protect each of said thin film transistors;
14	removing part of a gate insulating layer and said passivation film of each of
15	said thin film transistors in a region surrounded by said signal lines and said scanning
J ₁ 6	lines;
-1654	forming a color filter comprising a photosensitive color resist;
18	forming an overcoat layer on said color filter;
CSF C	patterning said overcoat layer;
20	forming a contact hole by patterning said color filter while using said overcoat
21	layer as a mask; and
22	forming a plurality of pixel electrodes comprising a transparent conductive
23	film electrically connected through said contact hole.
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